METHODS OF INCREASING WRITE SELECTIVITY IN AN MRAM

ABSTRACT OF THE DISCLOSURE

MRAM architectures are disclosed that produce an increased write margin and write selectivity without significantly reducing the packing density of the memory. The major axes of the magneto-resistive bits are offset relative to the axes of the digital lines to produce a magnetic field component from the digital line current that extends along the major axis of the magneto-resistive bits.

L:\DOCS\MSO\MSO-4447.DOC
070303